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Kind regards,

Team Nexperia

PMP5201V; PMP5201G; PMP5201Y

PNP/PNP matched double transistors

Rev. 03 — 28 August 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP matched double transistors in small Surface-Mounted Device (SMD) plastic packages. The transistors in the SOT666 and SOT363 (SC-88) packages are fully isolated internally.

Table 1. Product overview

Type number	Package		PNP/PNP h _{FE1} /h _{FE2}	NPN/NPN	
	NXP	JEITA	0.95 complement	complement	
PMP5201V	SOT666	-	PMP5501V	PMP4201V	
PMP5201G	SOT353	SC-88A	PMP5501G	PMP4201G	
PMP5201Y	SOT363	SC-88	PMP5501Y	PMP4201Y	

1.2 Features

- Current gain matching
- Base-emitter voltage matching
- Common emitter configuration for SOT353 types
- Application-optimized pinout

1.3 Applications

- Current mirror
- Differential amplifier

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
V_{CEO}	collector-emitter voltage	open base	-	-	-45	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	200	290	450	



PMP5201V; PMP5201G; PMP5201Y

PNP/PNP matched double transistors

Table 2. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
h _{FE1} /h _{FE2}	h _{FE} matching	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	[1] 0.98	1	-	
$V_{BE1}-V_{BE2}$	V _{BE} matching	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	[2] _	-	2	mV

^[1] The smaller of the two values is taken as the numerator.

2. Pinning information

Table 3. Pinning

Table 3.	Filling		
Pin	Description	Simplified outline	Symbol
SOT666 ;	SOT363		
1	base TR1		
2	base TR2	6 5 4	6 5 4
3	collector TR2		TR1 TR2
4	emitter TR2		
5	emitter TR1		1 2 3 006aaa550
6	collector TR1	001aab555	000aaa550
SOT353			
1	base TR1	П- П.	
2	emitter TR1, TR2	5 4	5 4
3	base TR2		TR1 TR2
4	collector TR2		
5	collector TR1	<u> </u>	1 2 3 006aaa551

3. Ordering information

Table 4. Ordering information

Type number	Package						
	Name	Description	Version				
PMP5201V	-	plastic surface-mounted package; 6 leads	SOT666				
PMP5201G	SC-88A	plastic surface-mounted package; 5 leads	SOT353				
PMP5201Y	SC-88	plastic surface-mounted package; 6 leads	SOT363				

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^[2] The smaller of the two values is subtracted from the larger value.

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Marking 4.

Table 5. Marking codes

Type number	Marking code ^[1]
PMP5201V	EC
PMP5201G	R5*
PMP5201Y	S9*

^{[1] * = -:} made in Hong Kong

Limiting values 5.

Limiting values Table 6.

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	–45	V
V_{EBO}	emitter-base voltage	open collector	-	- 5	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT666		[1][2]	200	mW
	SOT353		<u>[1]</u> _	200	mW
	SOT363		<u>[1]</u> _	200	mW
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT666		[1][2]	300	mW
	SOT353		<u>[1]</u> _	300	mW
	SOT363		<u>[1]</u> _	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

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^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

^[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

	_					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2]	-	625	K/W
	SOT353		<u>[1]</u> -	-	625	K/W
	SOT363		<u>[1]</u> -	-	625	K/W
Per device	ce					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2]	-	416	K/W
	SOT353		<u>[1]</u> -	-	416	K/W
	SOT363		<u>[1]</u> _	-	416	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
Per transis	Per transistor								
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V};$ $I_E = 0 \text{ A}$	-	-	–15	nA			
		$V_{CB} = -30 \text{ V};$ $I_{E} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	- 5	μΑ			
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V};$ $I_{C} = 0 \text{ A}$	-	-	-100	nA			
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \mu\text{A}$	-	250	-				
		$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	200	290	450				
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-50	-200	mV			
		$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	-	-200	-400	mV			
V_{BEsat}	base-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	<u>[1]</u> _	-760	-	mV			
		$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	<u>[1]</u> _	-920	-	mV			

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^[2] Reflow soldering is the only recommended soldering method.

Characteristics ...continued Table 8. T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{BE}	base-emitter voltage	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	[2] -600	-650	-700	mV
		$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA}$	[2] -	-	-760	mV
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	2.2	pF
C _e	emitter capacitance	$V_{EB} = -0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	10	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$	100	175	-	MHz
NF	noise figure	$V_{CE} = -5 \text{ V};$ $I_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 10 \text{ Hz to}$ 15.7 kHz	-	1.6	-	dB
		$V_{CE} = -5 \text{ V};$ $I_C = -0.2 \text{ mA};$ $R_S = 2 \text{ k}\Omega;$ $f = 1 \text{ kHz};$ $B = 200 \text{ Hz}$	-	3.1	-	dB
Per device						
h _{FE1} /h _{FE2}	h _{FE} matching	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	[<u>3</u>] 0.98	1	-	
$V_{BE1}-V_{BE2}$	V _{BE} matching	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	<u>[4]</u> _	-	2	mV

^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

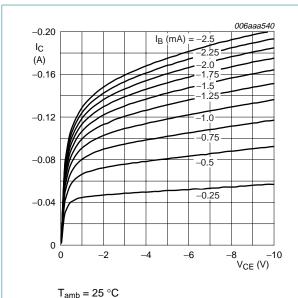
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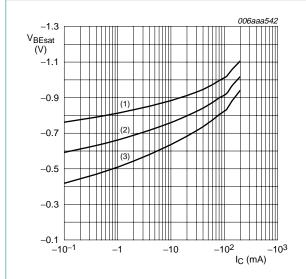
^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] The smaller of the two values is taken as the numerator.

^[4] The smaller of the two values is subtracted from the larger value.



Collector current as a function of Fig 1. collector-emitter voltage; typical values



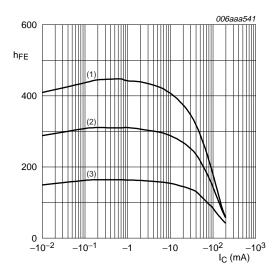
 $I_{\rm C}/I_{\rm B}=20$

(1) $T_{amb} = -55 \,^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 3. Base-emitter saturation voltage as a function of collector current; typical values



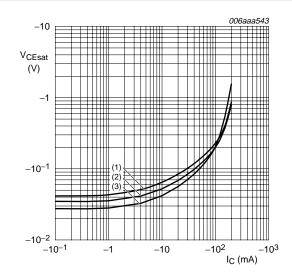
 $V_{CE} = -5 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \,^{\circ}C$

DC current gain as a function of collector Fig 2. current; typical values



 $I_C/I_B = 20$

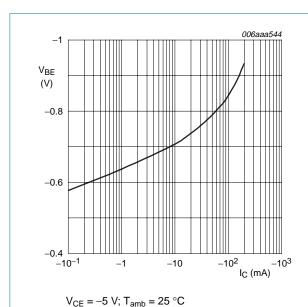
(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

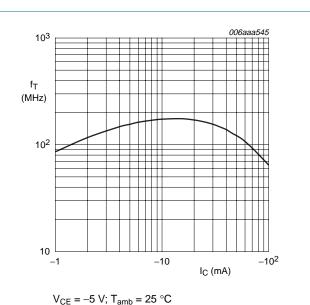
(3) $T_{amb} = -55 \, ^{\circ}C$

Collector-emitter saturation voltage as a Fig 4. function of collector current; typical values

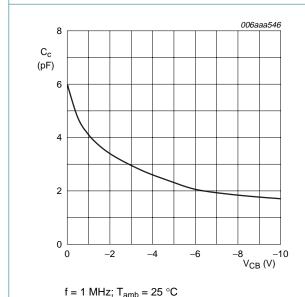
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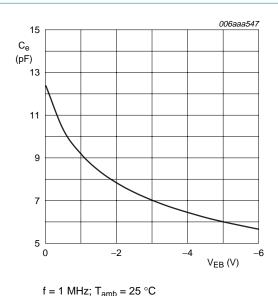
Base-emitter voltage as a function of collector Fig 5. current; typical values



Transition frequency as a function of collector Fig 6. current; typical values



Collector capacitance as a function of Fig 7. collector-base voltage; typical values

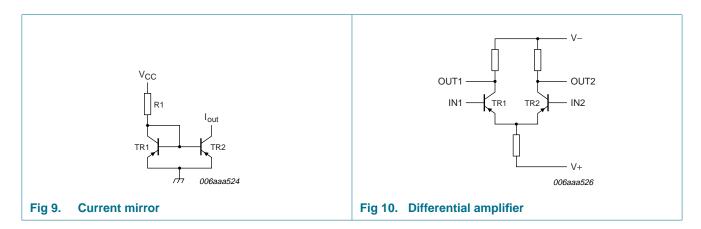


Emitter capacitance as a function of Fig 8. emitter-base voltage; typical values

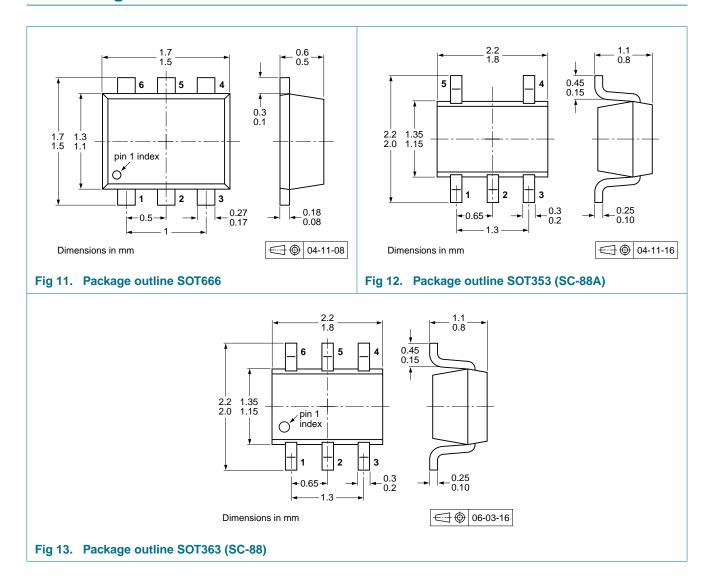
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8. Application information



9. Package outline



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10. Packing information

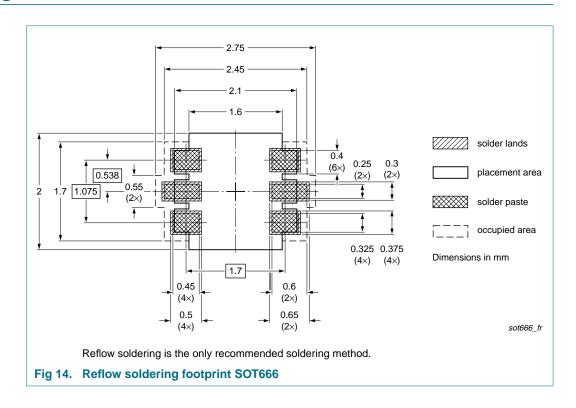
Table 9. **Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity			
				3000	4000	8000	10000
PMP5201V	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PMP5201G	SOT353	4 mm pitch, 8 mm tape and reel		-115	-	-	-135
PMP5201Y	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

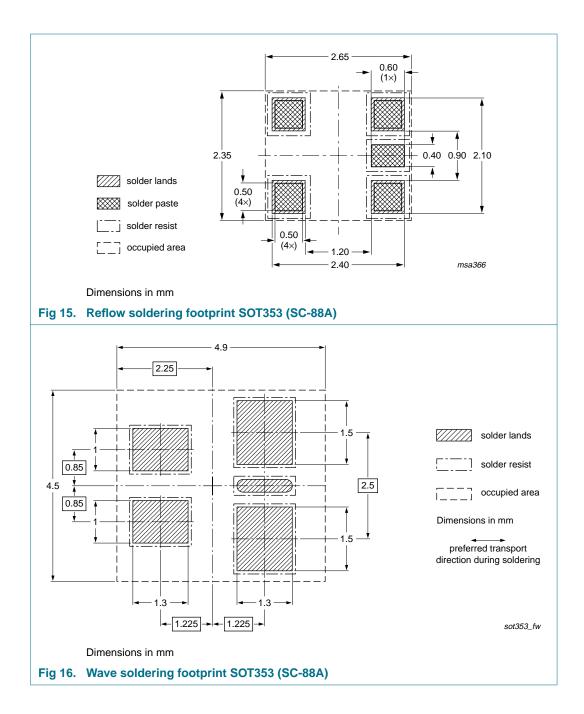
- For further information and the availability of packing methods, see Section 14.
- T1: normal taping
- T2: reverse taping

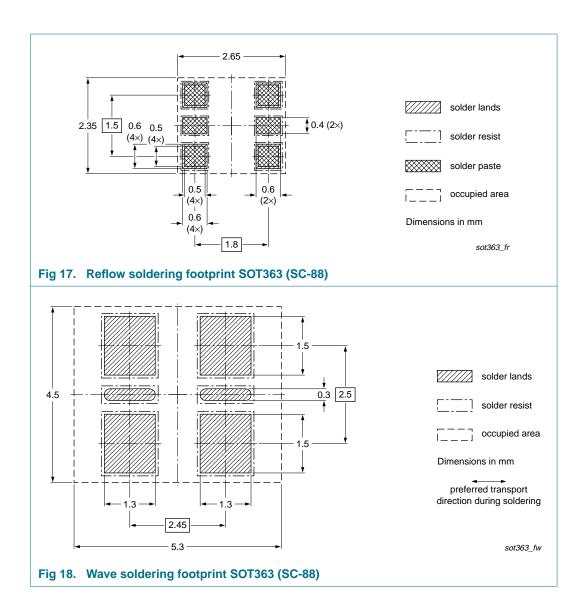
11. Soldering



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12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PMP5201V_G_Y_3	20090828	Product data sheet	-	PMP5201V_G_Y_2			
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 						
	• Figure 14 "R	eflow soldering footprint SOT6	66": updated				
	Figure 16 "W	ave soldering footprint SOT35	3 (SC-88A)": update	d			
	• Figure 17 "R	eflow soldering footprint SOT3	63 (SC-88)": update	d			
	• Figure 18 "W	ave soldering footprint SOT36	3 (SC-88)": updated				
PMP5201V_G_Y_2	20060914	Product data sheet	-	PMP5201G_Y_1			
PMP5201G_Y_1	20060214	Product data sheet	-	-			

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Product data sheet

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13. Legal information

13.1 **Data sheet status**

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NXP Semiconductors

PMP5201V; PMP5201G; PMP5201Y

PNP/PNP matched double transistors

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